Long You

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/341288/publications.pdf

Version: 2024-02-01

82 papers	4,427 citations	236612 25 h-index	102304 66 g-index
85 all docs	85 docs citations	85 times ranked	7102 citing authors

#	Article	IF	Citations
1	Current-Induced Magnetic Switching in an L10 FePt Single Layer with Large Perpendicular Anisotropy Through Spinâ€“Orbit Torque. Engineering, 2022, 12, 55-61.	3.2	3
2	Reconfigurable physical unclonable cryptographic primitives based on current-induced nanomagnets switching. Science China Information Sciences, 2022, 65, 1.	2.7	7
3	Asymmetrical magnetic domain wall motion in symmetrical heavy metal/ferromagnet multilayers. Physical Review B, 2022, 105, .	1.1	1
4	Terahertz bremsstrahlung and frequency comb induced by variable motion of an antiferromagnetic domain wall. Journal Physics D: Applied Physics, 2022, 55, 295302.	1.3	1
5	A three-dimensional magnetic field sensor based on a single spinâ€“orbit-torque device via domain nucleation. Applied Physics Letters, 2022, 120, .	1.5	2
6	Motion of skyrmioniums with negligible deformation in synthetic antiferromagnets. Applied Physics Letters, 2022, 121, .	1.5	3
7	Inâ€Memory Mathematical Operations with Spinâ€Orbit Torque Devices. Advanced Science, 2022, 9, .	5.6	4
8	Van der Waals Multiferroic Tunnel Junctions. Nano Letters, 2021, 21, 175-181.	4.5	53
9	Strain-induced Megahertz Oscillation and Stable Velocity of an Antiferromagnetic Domain Wall. Physical Review Applied, 2021, 15, .	1.5	7
10	Power and area efficient stochastic artificial neural networks using spinâ€“orbit torque-based true random number generator. Applied Physics Letters, 2021, 118, .	1.5	13
11	A spinâ€“orbit torque device for sensing three-dimensional magnetic fields. Nature Electronics, 2021, 4, 179-184.	13.1	28
12	Integrator based on current-controlled magnetic domain wall. Applied Physics Letters, 2021, 118, 052402.	1.5	1
13	Tunable Random Number Generators Implemented by Spin-Orbit Torque Driven Stochastic Switching of a Nanomagnet for Probabilistic Spin Logic. , 2021, , .		3
14	Reconfigurable Physical Unclonable Function Based on Spin-Orbit Torque Induced Chiral Domain Wall Motion. IEEE Electron Device Letters, 2021, 42, 597-600.	2.2	8
15	Ferroelectricâ€Nanocrack Switches for Memory and Complementary Logic with Zero Offâ€current and Low Operating Voltage. Advanced Electronic Materials, 2021, 7, 2100023.	2.6	4
16	Skyrmion devices for memory and logic applications. APL Materials, 2021, 9, .	2.2	89
17	Controlled nano-cracking actuated by an in-plane voltage. Science China Information Sciences, 2021, 64, 1.	2.7	0
18	Angle-Dependent Anisotropic Magnetoresistance Under the Competition Between Anisotropic Field and Magnetic Field. IEEE Transactions on Magnetics, 2021, 57, 1-7.	1.2	1

#	Article	IF	Citations
19	Skyrmion latch and flip-flop in magnetic nanotracks with gradient anisotropy. Journal of Magnetism and Magnetic Materials, 2020, 494, 165739.	1.0	4
20	A Dual Magnetic Tunnel Junctionâ€Based Neuromorphic Device. Advanced Intelligent Systems, 2020, 2, 2000143.	3.3	11
21	Synthesis and Properties of Monolayer Graphene (MLG)-Covered Fe(111). Chemistry of Materials, 2020, 32, 10463-10468.	3.2	1
22	Spinâ€“orbit torque-based reconfigurable physically unclonable functions. Applied Physics Letters, 2020, 116, .	1.5	15
23	Low-energy complementary ferroelectric-nanocrack logic. Nano Energy, 2020, 75, 104871.	8.2	3
24	Voltage-induced inertial domain wall motion in an antiferromagnetic nanowire. Journal of Magnetism and Magnetic Materials, 2020, 511, 166995.	1.0	7
25	Voltage-controlled magnetic anisotropy in antiferromagnetic L10-MnPt and MnPd thin films. Journal of Magnetism and Magnetic Materials, 2020, 505, 166758.	1.0	8
26	Voltage-controlled skyrmion-based nanodevices for neuromorphic computing using a synthetic antiferromagnet. Nanoscale Advances, 2020, 2, 1309-1317.	2.2	25
27	Thermally Assisted Skyrmion Memory (TA-SKM). IEEE Electron Device Letters, 2020, 41, 932-935.	2.2	3
28	Crack-Based Complementary Nanoelectromechanical Switches for Reconfigurable Computing. IEEE Electron Device Letters, 2020, 41, 784-787.	2.2	5
29	Spinâ€“Orbit Torque-Driven Magnetic Switching of Co/Pt-CoFeB Exchange Spring Ferromagnets. IEEE Transactions on Magnetics, 2019, 55, 1-4.	1.2	0
30	Spin-Dependent Transport in van der Waals Magnetic Tunnel Junctions with Fe₃GeTe₂ Electrodes. Nano Letters, 2019, 19, 5133-5139.	4.5	115
31	Nanoelectromechanical Switches by Controlled Switchable Cracking. IEEE Electron Device Letters, 2019, 40, 1209-1212.	2.2	6
32	Edge effects on the high-frequency dynamics of Dzyaloshinskii domain walls. Journal of Applied Physics, 2019, 126, 163904.	1.1	1
33	Voltage-induced high-speed DW motion in a synthetic antiferromagnet. Journal Physics D: Applied Physics, 2019, 52, 495001.	1.3	5
34	Large Magnetoresistance in an Electric-Field-Controlled Antiferromagnetic Tunnel Junction. Physical Review Applied, 2019, 12, .	1.5	8
35	Intrinsic Controllable Magnetism of Graphene Grown on Fe. Journal of Physical Chemistry C, 2019, 123, 26870-26876.	1.5	10
36	Spin-orbit-torque-driven multilevel switching in Ta/CoFeB/MgO structures without initialization. Applied Physics Letters, 2019, 114, .	1.5	31

#	Article	IF	Citations
37	A Spinâ€“Orbitâ€Torque Memristive Device. Advanced Electronic Materials, 2019, 5, 1800782.	2.6	51
38	Demonstration of spin transfer torque (STT) magnetic recording. Applied Physics Letters, 2019, 114, .	1.5	5
39	Shape transformation and self-alignment of Fe-based nanoparticles. Nanoscale Advances, 2019, 1, 2523-2528.	2.2	0
40	Edge effects on Dzyaloshinskii domain wall tilting. Journal of Magnetism and Magnetic Materials, 2019, 485, 69-74.	1.0	5
41	One-step fabrication of size-controllable nicotine containing coreâ€“shell structures. Nanoscale Advances, 2019, 1, 1305-1313.	2.2	0
42	Memristors: A Spinâ€“Orbitâ€Torque Memristive Device (Adv. Electron. Mater. 4/2019). Advanced Electronic Materials, 2019, 5, 1970022.	2.6	4
43	Effects of Interface Induced Natural Strains on Magnetic Properties of FeRh. Nanomaterials, 2019, 9, 574.	1.9	7
44	Voltage-Controlled Skyrmion Memristor for Energy-Efficient Synapse Applications. IEEE Electron Device Letters, 2019, 40, 635-638.	2.2	31
45	Motion of a skyrmionium driven by spin wave. Applied Physics Letters, 2018, 112, .	1.5	36
46	Reconfigurable Skyrmion Logic Gates. Nano Letters, 2018, 18, 1180-1184.	4.5	201
47	Electrically reversible cracks in an intermetallic film controlled by an electric field. Nature Communications, 2018, 9, 41.	5.8	53
48	3D multilevel spin transfer torque devices. Applied Physics Letters, 2018, 112, .	1.5	15
49	Binary and Ternary True Random Number Generators Based on Spin Orbit Torque. , 2018, , .		13
50	Readable racetrack memory via ferromagnetically coupled chiral domain walls. Applied Physics Letters, 2018, 113, .	1.5	4
51	Highly Secure Physically Unclonable Cryptographic Primitives Based on Interfacial Magnetic Anisotropy. Nano Letters, 2018, 18, 7211-7216.	4.5	36
52	Novel Cascadable Magnetic Majority Gates for Implementing Comprehensive Logic Functions. IEEE Transactions on Electron Devices, 2018, 65, 4687-4693.	1.6	8
53	Spin Dice Based on Orthogonal Spin-Transfer Devices With Planar Polarizer. IEEE Transactions on Magnetics, 2018, 54, 1-4.	1.2	2
54	Self-assembled single-digit nanometer memory cells. Applied Physics Letters, 2018, 113, 062404.	1.5	3

#	Article	IF	Citations
55	Magnetic skyrmions without the skyrmion Hall effect in a magnetic nanotrack with perpendicular anisotropy. Nanoscale, 2017, 9, 10212-10218.	2.8	48
56	Skyrmion-based high-frequency signal generator. Applied Physics Letters, 2017, 110, .	1.5	22
57	Interface Engineering of Domain Structures in BiFeO₃ Thin Films. Nano Letters, 2017, 17, 486-493.	4.5	69
58	Nonvolatile MoS2 field effect transistors directly gated by single crystalline epitaxial ferroelectric. Applied Physics Letters, 2017, 111, .	1.5	45
59	Epitaxial Growth of Intermetallic MnPt Films on Oxides and Large Exchange Bias. Advanced Materials, 2016, 28, 118-123.	11.1	24
60	Ferromagnetism: Epitaxial Growth of Intermetallic MnPt Films on Oxides and Large Exchange Bias (Adv. Mater. 1/2016). Advanced Materials, 2016, 28, 204-204.	11.1	0
61	Low current writing perpendicular magnetic random access memory with high thermal stability. Materials and Design, 2016, 92, 1046-1051.	3.3	11
62	Single crystal functional oxides on silicon. Nature Communications, 2016, 7, 10547.	5.8	156
63	Deterministic Domain Wall Motion Orthogonal To Current Flow Due To Spin Orbit Torque. Scientific Reports, 2015, 5, 11823.	1.6	64
64	Flexible spin-orbit torque devices. Applied Physics Letters, 2015, 107, .	1.5	26
65	Highly crystalline MoS2 thin films grown by pulsed laser deposition. Applied Physics Letters, 2015, 106, .	1.5	117
66	Switching of perpendicularly polarized nanomagnets with spin orbit torque without an external magnetic field by engineering a tilted anisotropy. Proceedings of the National Academy of Sciences of the United States of America, 2015, 112, 10310-10315.	3.3	236
67	Magnetoresistance oscillations in topological insulator Bi2Te3 nanoscale antidot arrays. Nanotechnology, 2015, 26, 265301.	1.3	3
68	Negative capacitance in a ferroelectric capacitor. Nature Materials, 2015, 14, 182-186.	13.3	611
69	Room-temperature antiferromagnetic memory resistor. Nature Materials, 2014, 13, 367-374.	13.3	546
70	Spin Hall effect clocking of nanomagnetic logic without a magnetic field. Nature Nanotechnology, 2014, 9, 59-63.	15.6	193
71	The effects of strain relaxation on the dielectric properties of epitaxial ferroelectric Pb(Zr0.2Ti0.8)TiO3 thin films. Applied Physics Letters, 2014, 105, .	1.5	11
72	Broad-Range Modulation of Light Emission in Two-Dimensional Semiconductors by Molecular Physisorption Gating. Nano Letters, 2013, 13, 2831-2836.	4.5	674

#	Article	IF	Citations
73	Interface control of bulk ferroelectric polarization. Proceedings of the National Academy of Sciences of the United States of America, 2012, 109, 9710-9715.	3.3	212
74	Possible route to low current, high speed, dynamic switching in a perpendicular anisotropy CoFeB-MgO junction using Spin Hall Effect of Ta. , 2012, , .		6
75	Co/Ni multilayers with perpendicular anisotropy for spintronic device applications. Applied Physics Letters, 2012, 100, .	1.5	73
76	Microscopic Origin of the Giant Ferroelectric Polarization in Tetragonal-like<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>BiFeO</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2011, 107, 147602.	2.9	290
77	Thermomagnetic writing on deep submicron-patterned TbFe films by nanosecond current pulse. Journal of Magnetism and Magnetic Materials, 2009, 321, 1015-1018.	1.0	10
78	Dynamic Heating in Micron- and Submicron-Patterned TbFe Films. Japanese Journal of Applied Physics, 2008, 47, 146-149.	0.8	10
79	Magnetic Force Microscopy Study of Thermomagnetic Writing on Micron- and Submicron-Patterned TbFe Films Using Current Pulses. Japanese Journal of Applied Physics, 2007, 46, 1003-1005.	0.8	4
80	The magnetic properties of sputter-deposited and annealed CoCr/CoCrPt recording media. Materials & Design, 2006, 27, 223-225.	5.1	4
81	Effect of Nb content on the microstructure and magnetic properties of CoCrPtNb/CrTi/C thin films. Journal of Alloys and Compounds, 2005, 388, 293-296.	2.8	0
82	The influence of annealing on the structural and magnetic properties of C/CoCrPt/CrTi trilayer recording media. Journal of Magnetism and Magnetic Materials, 2004, 280, 419-423.	1.0	2